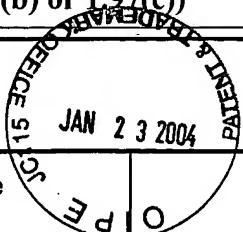


**TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT**  
(Under 37 CFR 1.97(b) or 1.97(c))

Docket No.  
SETI-0007

In Re Application: Shur et al.



Serial No.

10/696,693

Filing Date

10/29/2003

Examiner

Unknown

Group Art Unit

Unknown

**METHOD OF RADIATION GENERATION AND MANIPULATION**

**Payment of Fee**

(Only complete if Applicant elects to pay the fee set forth in 37 CFR 1.17(p))

- A check in the amount of \_\_\_\_\_ is attached.
- The Director is hereby authorized to charge and credit Deposit Account No. **500999** as described below.
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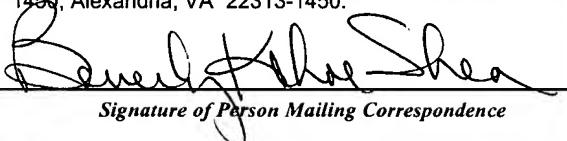
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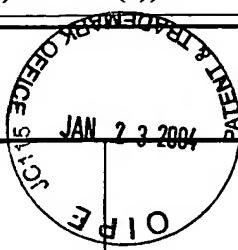
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**(Under 37 CFR 1.97(b) or 1.97(c))**

Docket No.  
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Serial No.  
10/696,693

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Examiner  
Unknown

Group Art Unit  
Unknown

Title: **METHOD OF RADIATION GENERATION AND MANIPULATION**

Address to:  
Commissioner for Patents  
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Alexandria, VA 22313-1450

**37 CFR 1.97(b)**

1.  The Information Disclosure Statement submitted herewith is being filed within three months of the filing of a national application other than a continued prosecution application under 37 CFR 1.53(d); within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; before the mailing of a first Office Action on the merits, or before the mailing of a first Office Action after the filing of a request for continued examination under 37 CFR 1.114.

**37 CFR 1.97(c)**

2.  The Information Disclosure Statement submitted herewith is being filed after the period specified in 37 CFR 1.97(b), provided that the Information Disclosure Statement is filed before the mailing date of a Final Action under 37 CFR 1.113, a Notice of Allowance under 37 CFR 1.311, or an Action that otherwise closes prosecution in the application, and is accompanied by one of:

the statement specified in 37 CFR 1.97(e);

**OR**

the fee set forth in 37 CFR 1.17(p).

**INFORMATION DISCLOSURE CITATION**  
*(Use several sheets if necessary)*

Docket Number (Optional) SETI-0007	Application Number 10/696,693
Applicant(s) Shur et al.	
Filing Date 10/29/2003	Group Art Unit Unkn wn

\*EXAMINER

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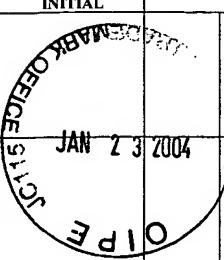
\*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>		Docket Number (Optional) SETI-0007	Application Number 10/696,693
		Applicant(s) Shur et al.	
		Filing Date 10/29/2003	Group Art Unit Unknown
*EXAMINER INITIAL	OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>		
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JAN 23 2004	"Resonant Detection and Frequency Multiplication of Terahertz Radiation Utilizing Plasma Waves in Resonant-Tunneling Transistors," V. Ryzhii et al., <i>Journal of Applied Physics</i> , Vol. 88, No. 5, September 2000, pp. 2868-2871.
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